C om parative study of the catalytic grow th of patterned carbon nanotube Im s

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Three di erent catalysts (Fe, Ni, Conitrates dissolved in ethanol) were patterned on a SiO $_2$ /Si substrate and multi-wall carbon nanotubes were grown by catalytic decomposition of acetylene. We compare the growth of the carbon nanostructures in the temperature range between 580 C and 1000 C.W ith our experimental set-up the catalyst solutions of cobalt and nickel were found to be less e cient than the one of iron. An optimal production of multi-wall nanotubes was observed at temperatures between 650 C and 720 C with the iron solution as catalyst. We found a tendency towards thicker structures with higher temperatures. Finally, we suggest a mechanism for the growth of these carbon structures.

I. IN TRODUCTION

Carbon nanostructures like fullerenes [1], nanotubes [2], nano-onions [3] and nano-homs [4] have attracted much interest recently. In particular their mechanical and electronic properties are the subject of intensive studies [5, 6]. Beside the fundam ental interest in their physical and chem ical properties, there are already som e applications based on carbon nanotubes. For example, they are capable to work as e cient eld em itters [7] and can form a basis for very robust bers [8]. N anotubes can be produced by arc discharge [2], by laserablation [9] or by chem ical vapor deposition techniques (CVD) [10, 11, 12, 13, 14, 15, 16]. CVD is currently the most promising and exible method with regard to applications, but our understanding of the in uence of the catalyst and the deposition parameters on the nanotube grow th is still fragm entary.

W e use here the CVD m ethod in com bination with m icrocontact printing to grow patterned Im s ofm ulti-wall carbon nanotubes [12]. M icrocontact printing (CP) has become an offen applied m ethod in the last few years because it is a simple way to de ne chem ical patterns on a variety of substrates [17, 18, 19]. W e use this m ethod to selectively deliver a catalyst to the substrate surface, which in turn activates the growth of nanotubes [12]. T he advantage of the patterning is that one can com pare the regions with and w ithout catalyst, and thus exactly determ ine the role of the catalyst. In order to better understand the catalytic growth we system atically exam ined the parameters temperature, catalyst composition and concentration.

II. EXPERIMENTALMETHODS

A. Synthesis of nano-structured m aterial

<100>-oriented boron doped silicon with the native SiD_2 oxide layer was used as substrate. The stamps for CP were prepared by curing poly (dim ethyl)siloxane (PDM S) for at least 12 h at 60 C on a structured master prepared by contact photolithography. The width of the square patterns on the wafer is 5 m. The stamps were subsequently hydrophilized by an oxygen plasm a treatment (O_2 pressure 0.8 mbar, bad coil power 75 W, 60 s). The stamp was baded with 0.2 m lof catalyst solution for 30 s and then dried in a nitrogen stream for 10 s.

The solutions were $Fe(NO_3)_3$ 9HO, $Ni(NO_3)_2$ 6HO or $Co(NO_3)_2$ 6HO dissolved in ethanolat concentrations between 50 and 200 m M. The solutions were used 12 h after preparation because the m etallic ions in the solution form chem ical com plexes which become larger with time. A period of 12 h for this \aging" of the solution was found to be ideal for the catalytic growth of nanotubes [12]. The printing was performed by placing the stam p on the surface of the SiO₂/Siwafer for 3 s.

The sam ples were placed in a horizontal ow reactor (quartz tube of 14 mm diam eter in a horizontal oven) directly after the printing. The treatment in the CVD oven proceeded in three steps. In the rst step, the catalyst was annealed for 20 m in under a ow of 80 m 1/m in of nitrogen to roughen the surface of the catalyst and to

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clean the reactor atm osphere. The actual deposition was perform ed with 80 m l/m in of nitrogen plus 20 m l/m in of acetylene (carbon source for the catalytic growth) at atm ospheric pressure for 30 m in. The third step was a nal annealing of 10 m in. under 80 m l/m in of nitrogen. The same tem perature was used throughout the entire procedure, which im plies that a change of the tem perature a ected all the steps.

B. Characterization techniques

Scanning electron m icroscopy (SEM) was performed to analyze the m icrostructures in plan view. A Philips XL 30 m icroscope equipped with a eld em ission gun (FEG) operating at an acceleration voltage between 2 and 5 kV, a working distance of typically 10 mm, and in secondary electron (SE) in age mode was used.

The growth morphology of the tubular structures and their crystallinity were controlled by transmission electron microscopy (TEM). For this purpose a Philips EM 430 microscope equipped with a Gatan image plate operating at 300 kV (point resolution 0.3 nm) was used.

III. RESULTS

W e studied system atically the in uence of (a) the catalyst solutions containing iron, nickel or cobalt ions, (b) the deposition temperature and (c) the concentration of the catalyst on the nanotube growth. W e used concentrations of 50 m M and 100 m M of the three catalysts at temperatures between 580 C and 1000 C in 70 C steps. For the catalyst iron, which produced the highest am ount of nanotubes, we also exam ined sam ples with a concentration of 150 m M and 200 m M at 650 C.

A fler the catalytic growth of the structures, the observation by SEM showed a hom ogeneous growth over the whole sample surface (> 1 cm², Fig. 1). The nanotubes grow only where the catalyst has been printed, and the bare substrate is free of any carbon form for growth tem peratures below 800 C.

As displayed in Fig. 2, we found that the use of the iron catalyst resulted in the highest delity of replication of the square pattern, whereas the use of a pure nickel or cobalt solution resulted in inferior patterning. Because of the wetting behavior on the stam p [12], the nickel and the cobalt solutions produced one drop on each square structure of the stam p, which were transferred to the substrate. As a result, the patterns obtained with cobalt and nickel are sm all and of irregular, circle-like shape. At concentrations higher than 100 mM the printing of the iron solution became also more di cult. XPS and TEM experiments have shown that the printed iron catalyst consists of a gel-like material of partially hydrolyzed Fe (III) nitrate that form sa porous and continuous Fe₂O₃

In after annealing [20]. We assume that the printed catalysts nickel and cobalt are of a similar structure. The comparison of the three catalysts shows that iron produced the highest density of carbon structures at any considered temperature, as seen in Fig. 2. Nickel and cobalt turned out to be not as good catalysts as iron, as we found only few nanotubes at 720 C with 100 m M nickel and cobalt solutions. At 1000 C, the printed nickel and the cobalt solution initiated the growth of spherical carbon structures, and iron caused the growth of thick worm -like structures.

There is a tendency towards thicker structures with increasing tem perature [21], as shown in Fig. 3 for iron. The catalytic growth of nanotubes started at a tem perature of 620 C, but we observed only a few nanotubes at this tem perature. A uniform coverage of each printed square was obtained at tem peratures of 650 C and higher. The thinnest nanotubes were found at 650 C with iron as catalyst. The highest density of nanotubes was observed at 720 C.U sing catalyst concentrations of 100 m M we found relatively thick worm -like structures at tem peratures exceeding 930 C (\carbon worm s"). These structures grew to a diameter of up to 1 m. Furtherm ore, the acetylene starts to dissociate in the gas phase at tem peratures above 800 C and the resultant carbon form s a am orphous continuous layer on the silicon surface of all sam ples. This layer gets also thicker with the tem perature.

Fig. 4 shows clearly that the use of higher catalyst concentrations resulted in an increase of the nanotube density. The nanotubes reached lengths of several m with a diameter up to 25 nm. Transmission electron microscopy (TEM) of the samples obtained at 650 C using the 50 mM iron catalyst con med that the structures are well-graphitized and well-separated multiwalled nanotubes which are not lled (Fig. 5). Most of them have open ends and some nanotubes contain encapsulated catalyst particles. These particles are aligned in the growth direction and of prolate shape. They have diameters of about 8 nm and lengths of about 16 nm.

IV. DISCUSSION

We suppose that the mechanism of the catalytic growth of carbon nanotubes is similar to the one described by K anzow et al. [22]. The acetylene is dissociated catalytically at facets of well de ned crystal orientation of a small metal (oxide) particle. The resulting hydrogen H_2 is removed by the gas ow whereas the carbon di uses into the particle. For unsaturated hydrocarbons this process is highly exotherm ic. When the particle is saturated with carbon, the carbon segregates on another, less reactive surface of the particle, which is an endotherm ic process. The resulting temperature gradient supports the di usion of carbon through the particle. To avoid dangling bonds, the carbon atom s assemble in a sp^2 structure at the cooler side of the particle, which leads to the form ation of a nanotube.

The growth of nanotubes starts at tem peratures of

620 C because there is enough mobility of the atom s of the catalyst to enable the di usion of the carbon through the particle and to start the dynam ic of the catalytic construction of carbon nanotubes. At tem peratures above 800 C the acetylene starts to dissociate already in the gas phase. The carbon in the gas ow of acetylene and nitrogen form s carbon akes which will be adsorbed on the surface of the sam ple as well as on the surface of the structures (see R ef. [23]). Since the acetylene is not com – pletely dissociated and the catalytic grow th proceeds, the nanotubes will still grow and be covered with a layer of carbon form ed by the carbon akes. The structures get thicker with tem perature because the proportion between dissociated and m olecular acetylene increases.

W e found only few nanotubes using nickel and cobalt as catalysts, whereas other groups successfully used nickel [13, 15], nickel-cobalt [14] or cobalt [11]. This may be due to several facts. First, the catalyst is usually deposited by therm al evaporation or sputtering from a pure m etal source. Furtherm ore, the catalyst is often reduced before the growth or the growth itself is carried out in a reducing atm osphere to ensure that the catalyst rem ains m etallic [24]. In our case how ever, the catalyst is dissolved in a solution. Since the printed iron catalyst consists of a gel-like material that forms a Fe_2O_3 Im after annealing [12] and no step is taken to reduce the catalyst, we conclude that in our case the catalyst is not pure metal, but metal oxide. This may signi cantly change the behavior of the catalyst. Second, we use therm al CVD, in contrast to the Hot Filam ent or Plasm a Enhanced CVD used in other studies. The hot lament and the plasm a provides an additional possibility for the dissociation of the hydrocarbon and may

The electronic properties and the enormous lengthdiameter ratio of the carbon nanotubes of ers the possibility to use them as eld em itters [7]. The non-aligned arrangement of the carbon nanotubes is known to be even more e cient in eld em ission than an aligned one [25]. The em ission from aligned nanotube lm s is lower because of screening e ects between densely packed neighboring tubes and the small height of the few protruding tubes. In contrast, the non-aligned lm s of er well sep-

arated nanotubes which do not show these e ects [26]. For the sake of pro tability their application in eld em ission displays requires glass as substrate instead of silicon, but the borosilicate glass used m elts around 660 C.M ost studies carried out on catalytic nanotube growth use however tem peratures above 700 C [11, 14], which are too high for that purpose. Choi et al. report a plasm aenhanced CVD process at a tem perature of 550 C [15], but the diam eter of these nanotubes seems quite large and lacks uniform ity. We could demonstrate that the grow th of thin carbon nanotubes with just a few layers of carbon starts around 620 C, and that high quality Im s are obtained at 650 C. These nanotubes have uniform diam eter and well-graphitized walls which is an indicator for good eld em ission properties. The tem perature may even be further low ered by using other gas m ixtures, by using other m etallic or heterogeneous catalysts [16].

V. CONCLUSIONS

We observed a signi cant in uence of the tem perature and the catalyst material on the quality of the carbon nanostructures. The diameter of the nanotubes and the density is adjustable by choosing the corresponding tem – perature and/or the concentration of the catalyst solution. Under the studied conditions iron is the best catalyst. We observed a morphology transition with tem – perature from multi-wall nanotubes to \carbon worm s". The best nanotubes are obtained at tem peratures between 650 C and 720 C. Nanotubes obtained at tem – peratures below the melting tem perature of borosilicate glass of 660 C are suitable as eld em itters for at panel displays.

A cknow ledgem ent

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F igures



alyst on the nanotube growth: 100 m M solution of (a) Fe (b) Ni(c) Conitrate at 720 C and of (d) Fe (e) Ni(f) Conitrate



FIG.1: SEM m icrograph demonstrating the hom ogeneity of the patterning on a Si/SiO₂ sample (100 m M iron nitrate solution at 720 C)



FIG.3: SEM m icrographs dem on strating the e ect of the tem perature on the nanotube growth: 100 m M solution of iron nitrate at (a) 580 C (b) 650 C (c) 720 C (d) 860 C (e) 930 C (f) 1000 C



FIG.4: SEM m icrographs demonstrating the e ect of the concentration on the nanotube growth: a (a) 50 m M (b) 100 m M (c) 150 m M (d) 200 m M solution of iron nitrate at 650 C



FIG.5: TEM m icrograph of individual nanotubes grown at 650 C with a 50 m M iron solution.